

Appl. No. 10/642,856
Amdt. dated 9/19/06
Reply to Office action of 6/19/06

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended). A method for writing to magnetoresistive memory cells of an MRAM memory, the magnetoresistive memory cells having a multilayer system containing layers stacked one above another, the layers including a soft-magnetic layer, a hard-magnetic layer and a tunnel oxide layer disposed between the soft-magnetic layer and the hard-magnetic layer, which comprises the steps of:

impressing write currents being in each case impressed on a respective word line and a respective bit line resulting in a superposition of magnetic fields generated by the write currents, and in each selected memory cell selected by the respective word line and the respective bit line, a magnetic field leads to a change of a magnetization direction of only the soft-magnetic layer, the write currents being impressed on the respective word line and the respective bit line ~~in a manner temporally offset with respect to one another, resulting in the magnetization direction of the soft magnetic layer in the selected memory cell being rotated~~ causing the magnetic field produced by the superposition of the magnetic

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fields of the word line current and a bit line current to be
precisely large enough to suffice for switching the
magnetization of the soft magnetic layer in the selected
memory cell but small enough that neither adjacent cells nor
cells situated on the selected lines are switched, the
timings of the impression of both the word line current and
the bit line current being exactly controlled so that the
conventional switching of the soft magnetic layer of the
selected memory cell is transferred into a magnetization
rotation process rotating said magnetization direction of the
soft magnetic layer in a plurality of successive steps in a
direction desired for writing a logic "0" or "1".

Claim 2 (currently amended). The method according to claim 1, which further comprises impressing the write currents for the selected memory cell in each case in approximately a same duration and in a manner ~~temporally offset with respect to one another~~ offset in time with respect to one another by half of their switching duration.

Claim 3 (canceled).

Claim 4 (currently amended). An MRAM memory configuration, comprising:

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an array containing magnetoresistive memory cells each having a multilayer system with layers stacked one above another, said layers including a soft-magnetic layer, a hard-magnetic layer, and a tunnel oxide layer disposed between said soft-magnetic layer and said hard-magnetic layer;

word lines;

bits lines crossing said word lines at each of said magnetoresistive memory cells; and

a writing control circuit for impressing write currents in each case onto a respective word line and a respective bit line of a respective memory cell selected for writing, said writing control circuit having a write circuit for impressing the write currents in each case on said respective word line and said respective bit line ~~in a manner temporally offset with respect to one another, resulting in a magnetization direction of only said soft magnetic layer of said respective memory cell being~~ causing the magnetic field produced by the superposition of the magnetic fields of the word line current and a bit line current to be precisely large enough to suffice for rotating the magnetization of the soft magnetic layer in the selected memory cell but small enough that neither adjacent cells nor cells situated on the selected

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lines are switched, said write circuit controlling the
timings of the impression of both said word line current and
said bit line current exactly causing the conventional
switching of the soft magnetic layer of the selected memory
cell to be transferred into a magnetization rotation process
with only the soft magnetic layer of the respective memory
cell being rotated in a plurality of successive steps in a
direction desired for writing a logic "0" or "1".

Claim 5 (new). The method according to claim 1, wherein in
order to write a logic "1" to the selected memory cell the
write current in the bit line is impressed in the same
current flow direction as the flowing of the write current of
the word line and is impressed in a delayed manner relative
to the write current of the word line.

Claim 6 (new). The method according to claim 2, wherein in
order to write a logic "1" to the selected memory cell the
write current in the bit line is impressed in the same
current flow direction as the flowing of the write current of
the word line and is impressed in a delayed manner relative
to the write current of the word line.

Claim 7 (new). The method according to claim 1, wherein the
plurality of successive steps of the rotation of the

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magnetization direction of the soft magnetic layer comprises:

a first rotating step, when the write current flows only in the word line for rotating the magnetization direction of the soft magnetic layer of the selected memory cell by an angle between 0° and 90° with respect to its original magnetization direction;

a second rotating step, when the write currents flow in both the word line and the bit line for rotating the magnetization direction of the soft magnetic layer of the selected memory cell by an angle between 90° and 180° with respect to its original magnetization direction; and

a third rotation step, when the write current flows only in the bit line for further rotating the magnetization direction of the soft magnetic layer into the desired final state in which the magnetization direction of the soft magnetic material differs by 180° with respect to its original magnetization direction.